ABSTRACT

A semiconductor device may include a substrate including first and second active regions, which are adjacent to each other, first and second active patterns provided on the first and second active regions, respectively, and a gate electrode extended to cross the first and second active patterns. The gate electrode may include first and second electrode portions provided on the first and second active regions, respectively. The second electrode portion may include a first metal pattern, an etch barrier pattern, a second metal pattern, and a third metal pattern sequentially covering the second active pattern. The first electrode portion may include a second metal pattern covering the first active pattern. The etch barrier pattern may be in contact with the first metal pattern and the second metal pattern, and the etch barrier pattern may be thinner than the first metal pattern and thinner than the second metal pattern.

FIG. 2E